

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (currently amended): An infrared sensor comprising:

an image region containing thermoelectric conversion pixels arranged two-dimensionally in the form of a matrix of a plurality of row and a plurality of columns on a semiconductor substrate to detect incident infrared rays;

a plurality of row selection lines arranged in the column direction in the imaging region;

a plurality of signal lines arranged in the row direction in said imaging region;

a plurality of amplifier transistors having respective gates connected to said signal lines and adapted to be modulated by the respective signal voltages generated in the signal lines;

a plurality of storage capacities connected respectively to the drains of the amplifier transistors and configured to store signal charges from the transistors;

a plurality of reset circuits connected to the respective drains of said amplifiers to reset the drain potentials of said amplifier transistors and make them show a predetermined potential;

a plurality of read circuits configured to read the respective signal charges stored in said storage capacities;

a plurality of coupling capacities arranged respectively between said signal lines and the gates of said amplifier transistors; and

a plurality of sampling transistors connected respectively between the drains and the gates of said amplifier transistors, said sampling transistors being selectively turned on to sample threshold voltages of amplifier transistors to the gates thereof.

Claim 2 (original): An infrared sensor according to Claim 1, wherein
said imaging region includes at least a row of insensitive pixels having no sensitivity to infrared rays in said thermoelectric conversion pixels.

Claim 3 (currently amended): An infrared sensor according to Claim 1, wherein
said imaging region includes at least a row of insensitive pixels having no sensitivity to infrared rays in said thermoelectric conversion pixels arranged in the form of a matrix of a plurality of row and a plurality of columns and

said infrared sensor further comprises:

a storage circuit configured to store a first grouped pieces of row output information obtained from said read circuits on a time series ~~bases~~ basis; and

a correction circuit configured to correct a second grouped pieces of row output information obtained as a result of selecting a row different from the row used for obtaining the first grouped pieces of row output information on the basis of the first grouped pieces of row output information stored in the storage circuit.

Application No. New Divisional Application
Inventor: Yoshinori IIDA et al.
Title: INFRARED SENSOR

PATENT
Atty. Docket No. 245810US-2TTCRD

Claim 4 (original): An infrared sensor according to Claim 1, wherein
said imaging region contains at least two rows of insensitive pixels having no
sensitivity to infrared rays.

Claims 5 - 16 (Canceled)